OptiMOS®-T Power-Transistor

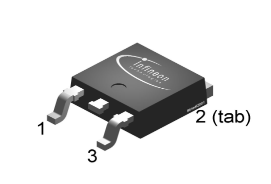
Product Summary

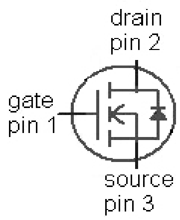
V_{DS}	100	V
$R_{DS(on),max}$	11.5	mΩ
I_D	70	A

Features

- N-channel - Enhancement mode
- Automotive AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested

PG-TO252-3-11





Type	Package	Marking
IPD70N10S3L-12	PG-TO252-3-11	QN10L12

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25°C, V_{GS}=10V	70	A
		T_C=100°C, V_{GS}=10V[1)]	48	
Pulsed drain current[1)]	$I_{D,pulse}$	T_C=25°C	280	
Avalanche energy, single pulse[1)]	E_{AS}	I_D=35A	410	mJ
Avalanche current, single pulse	I_{AS}		70	A
Gate source voltage[2)]	V_{GS}		±20	V
Power dissipation	P_{tot}	T_C=25 °C	125	W
Operating and storage temperature	T_j, T_{stg}		-55 ... +175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics[1)]						
Thermal resistance, junction - case	R_{thJC}		-	-	1.2	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm^2 cooling area[3)]	-	-	40	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D= 1mA	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=83µA	1.2	1.7	2.4	
Zero gate voltage drain current	I_{DSS}	V_{DS}=80V, V_{GS}=0V, T_j=25°C	-	0.01	0.1	µA
		V_{DS}=80V, V_{GS}=0V, T_j=125°C[1)]	-	1	10	
Gate-source leakage current	I_{GSS}	V_{GS}=16V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=4.5V, I_D=70A	-	11.7	15.2	mΩ
		V_{GS}=10 V, I_D=70 A	-	9.6	11.5	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics[1]						
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	4270	5550	pF
Output capacitance	C_{oss}		-	950	1235	
Reverse transfer capacitance	C_{rss}		-	90	135	
Turn-on delay time	$t_{d(on)}$	V_{DD}=20V, V_{GS}=10V, I_D=70A, R_G=3.5Ω	-	12	-	ns
Rise time	t_r		-	6	-	
Turn-off delay time	$t_{d(off)}$		-	35	-	
Fall time	t_f		-	7	-	
Gate Charge Characteristics[1]						
Gate to source charge	Q_{gs}	V_{DD}=80V, I_D=70A, V_{GS}=0 to 10V	-	16	21	nC
Gate to drain charge	Q_{gd}		-	11	17	
Gate charge total	Q_g		-	59	77	
Gate plateau voltage	$V_{plateau}$		-	3.7	-	V
Reverse Diode						
Diode continous forward current[1]	I_S	T_C=25°C	-	-	70	A
Diode pulse current[1]	$I_{S,pulse}$		-	-	280	
Diode forward voltage	V_{SD}	V_{GS}=0V, I_F=70A, T_j=25°C	0.6	1	1.2	V
Reverse recovery time[1]	t_{rr}	V_R=50V, I_F=I_S, di_F/dt=100A/µs	-	80	-	ns
Reverse recovery charge[1]	Q_{rr}		-	185	-	nC

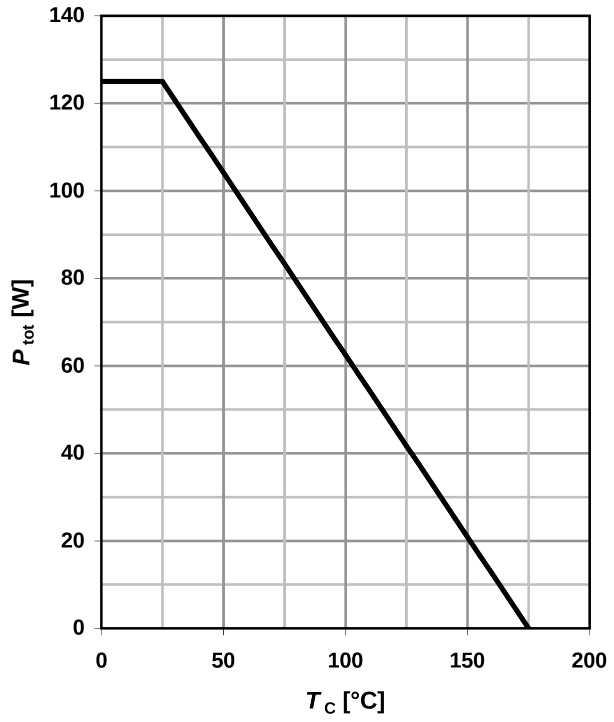
[1] Defined by design. Not subject to production test.

[2] Qualified with V_{GS} = +20/-5V.

[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

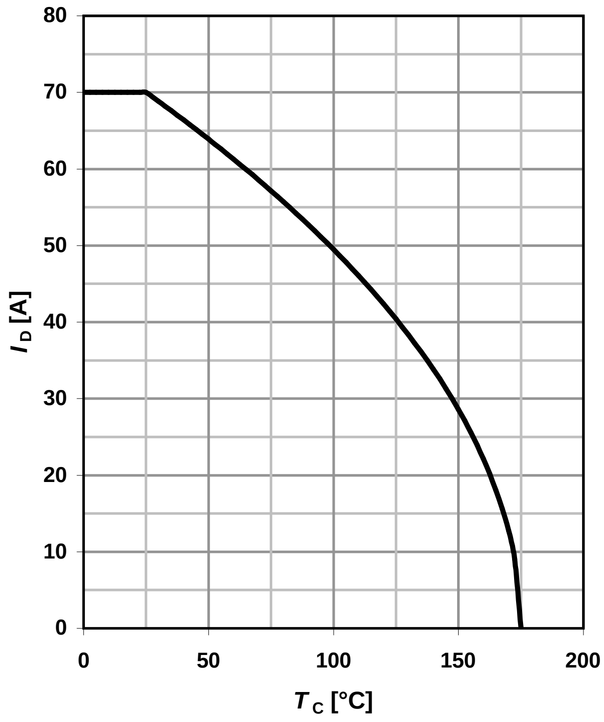
1 Power dissipation

$P_{tot} = f(T_C)$; $V_{GS} \geq 6$ V



2 Drain current

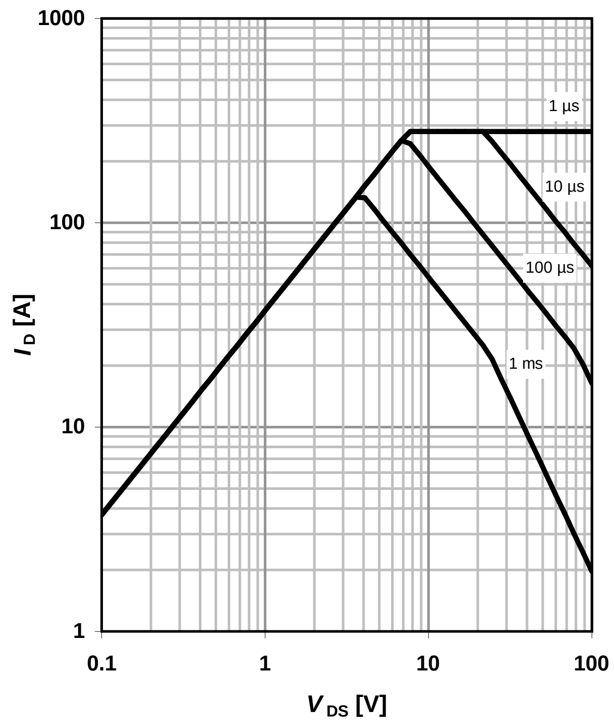
$I_D = f(T_C)$; $V_{GS} \geq 6$ V



3 Safe operating area

$I_D = f(V_{DS})$; $T_C = 25$ °C; $D = 0$

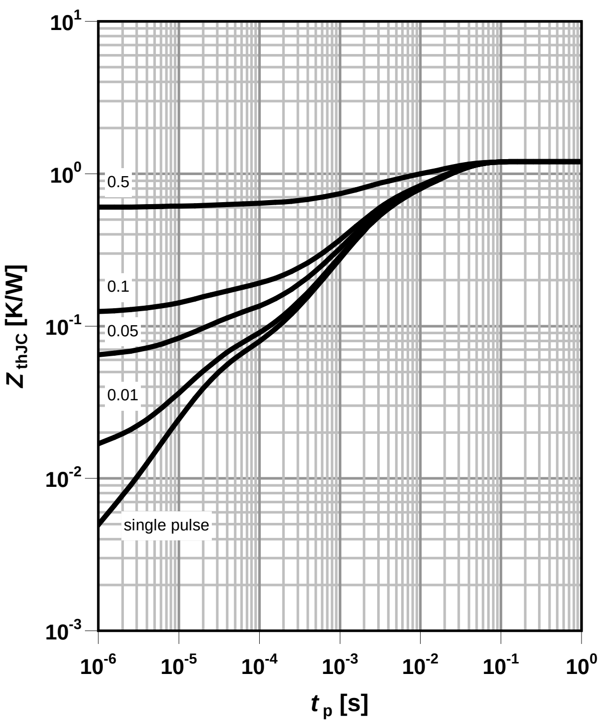
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

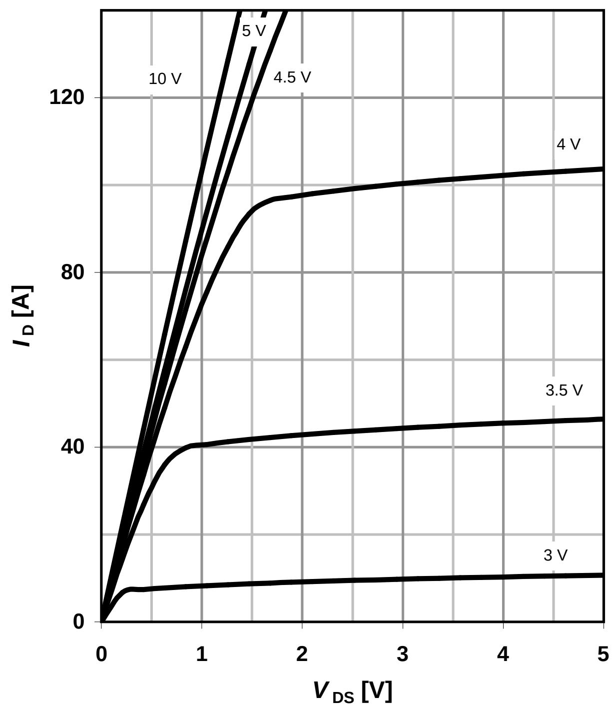
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS})$; $T_j = 25$ °C

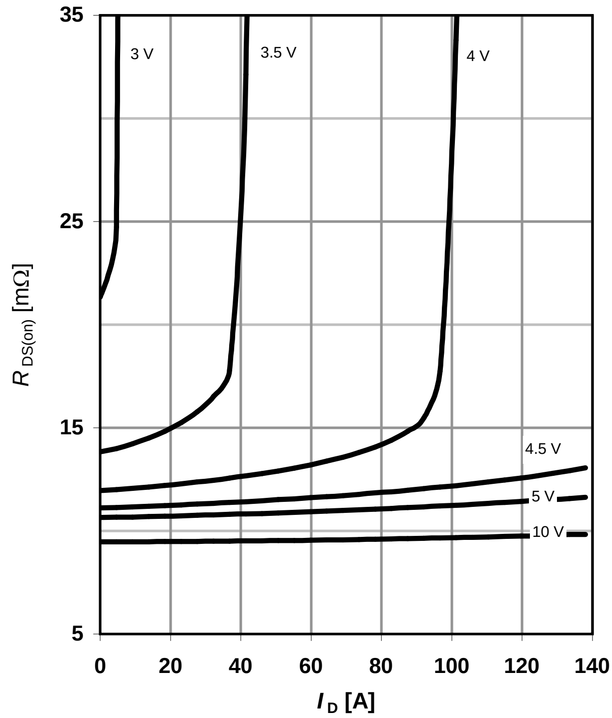
parameter: V_{GS}



6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D)$; $T_j = 25$ °C

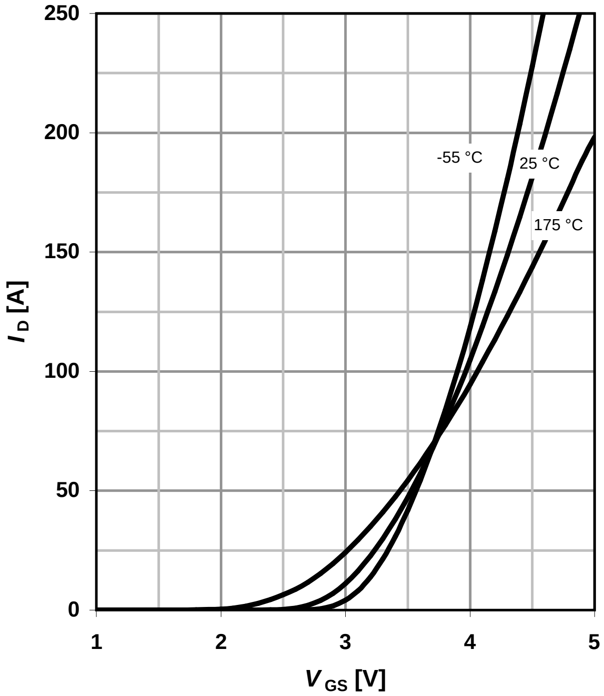
parameter: V_{GS}



7 Typ. transfer characteristics

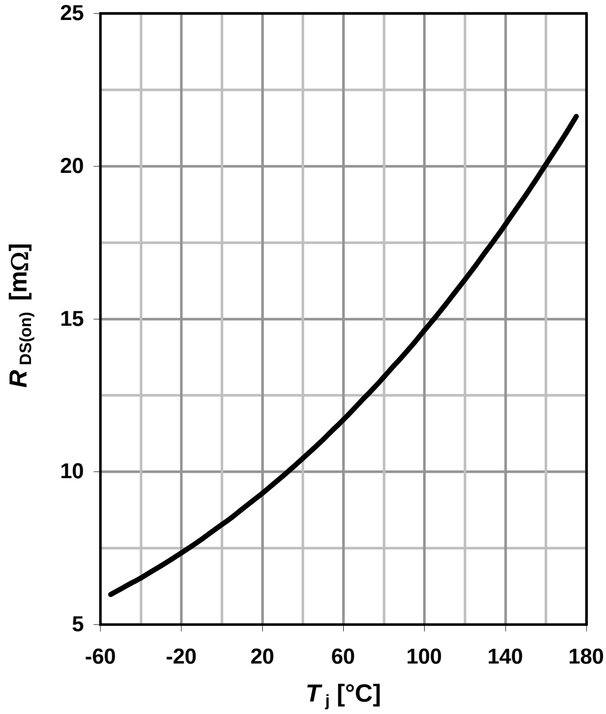
$I_D = f(V_{GS})$; $V_{DS} = 6V$

parameter: T_j



8 Typ. drain-source on-state resistance

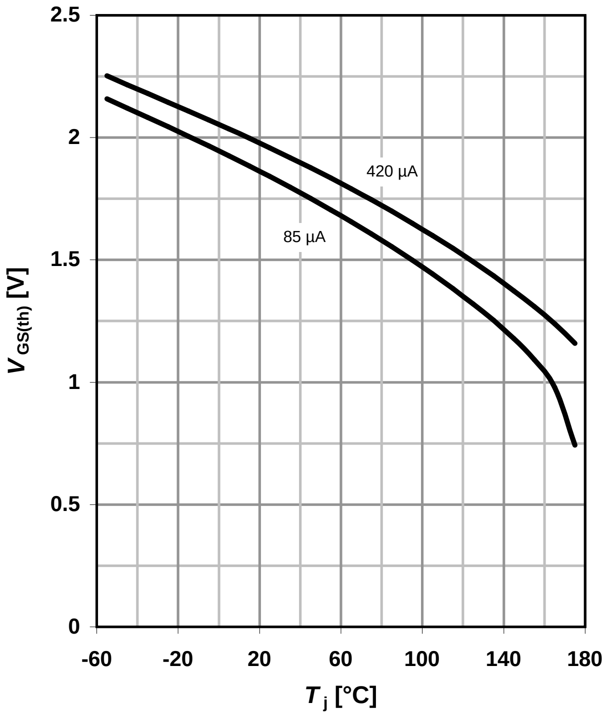
$R_{DS(on)} = f(T_j)$; $I_D = 70$ A; $V_{GS} = 10$ V



9 Typ. gate threshold voltage

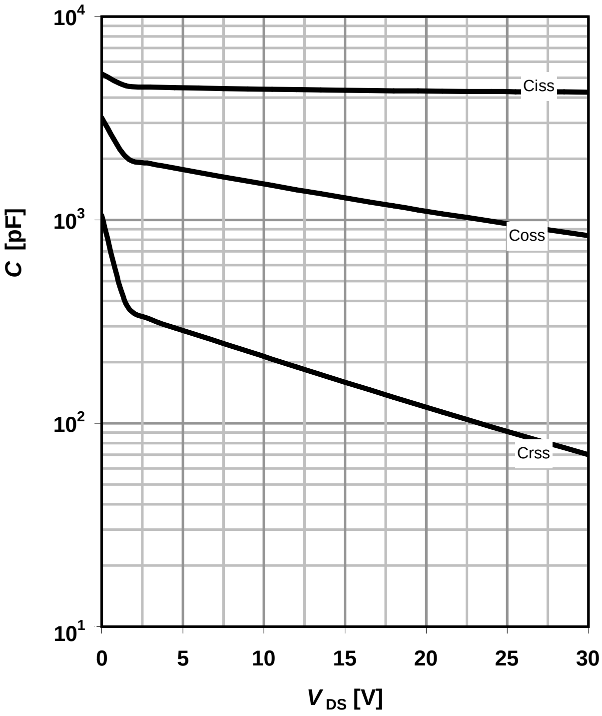
$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$

parameter: I_D



10 Typ. capacitances

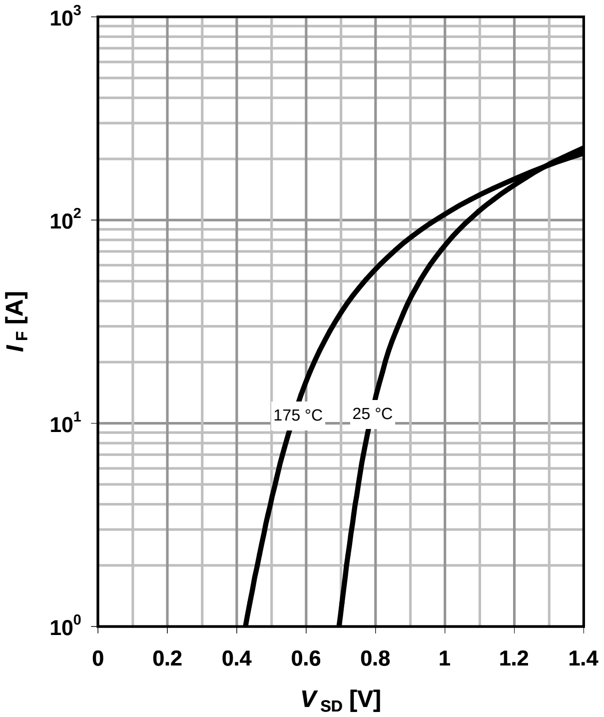
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz



11 Typical forward diode characteristicis

IF = $f(V_{SD})$

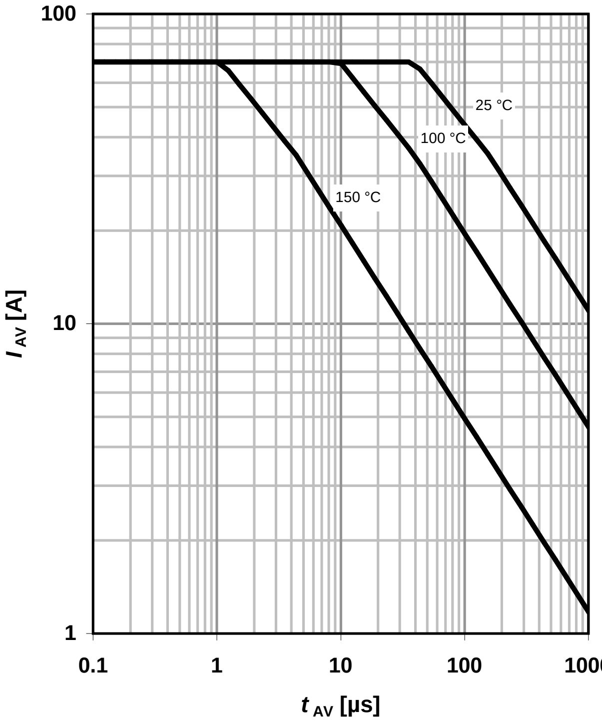
parameter: T_j



12 Typ. avalanche characteristics

$I_{AS} = f(t_{AV})$

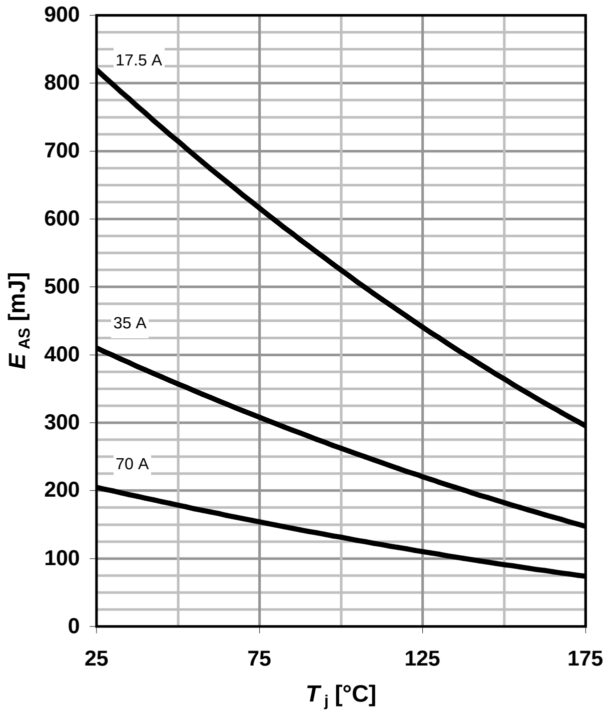
parameter: $T_{j(start)}$



13 Typical avalanche energy

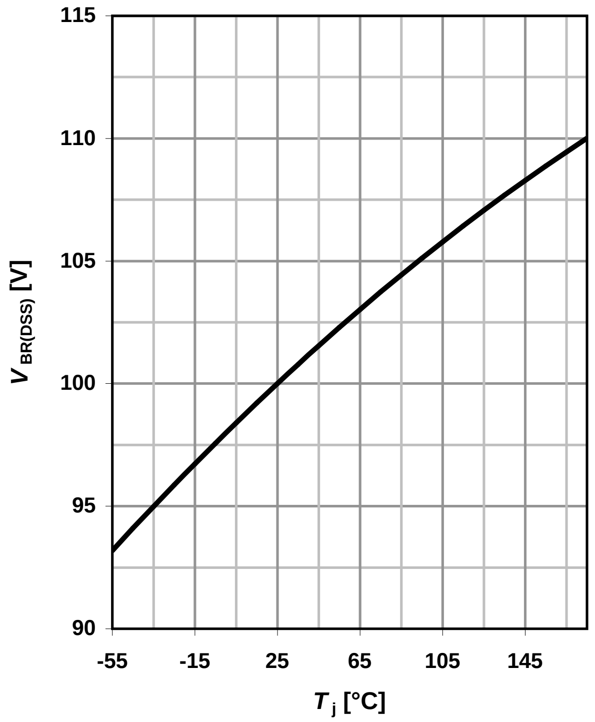
$E_{AS} = f(T_j)$

parameter: I_D



14 Typ. drain-source breakdown voltage

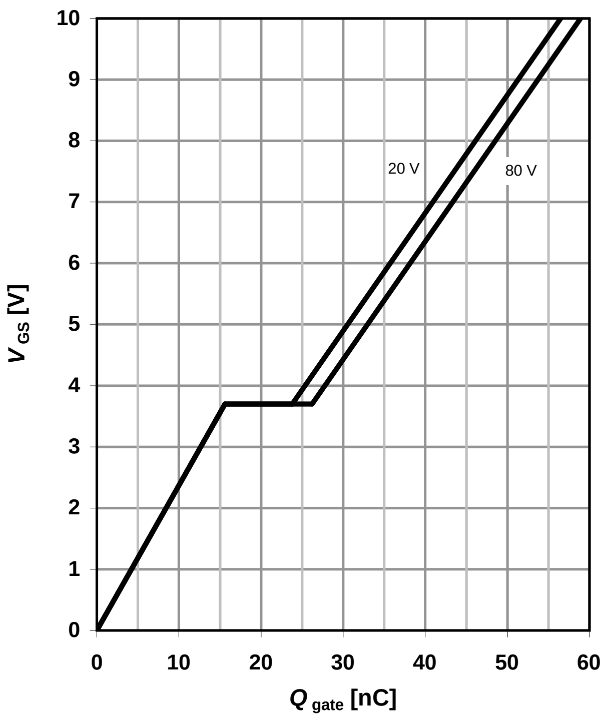
$V_{BR(DSS)} = f(T_j)$; $I_D = 1$ mA



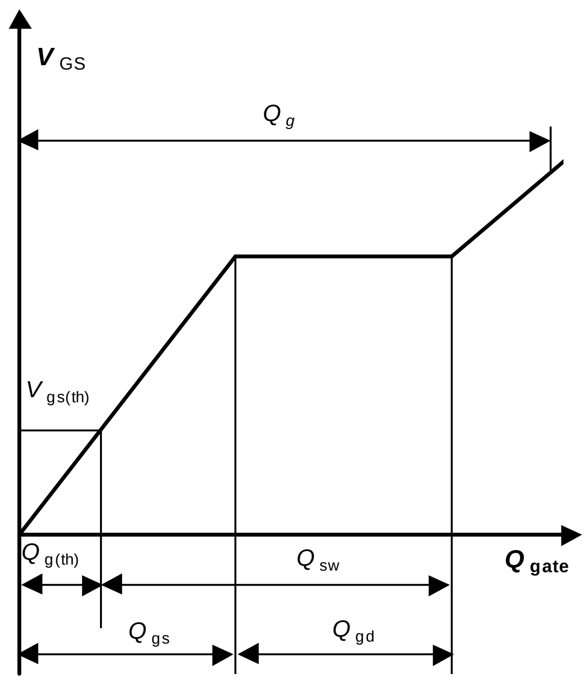
15 Typ. gate charge

$V_{GS} = f(Q_{gate})$; $I_D = 70$ A pulsed

parameter: V_{DD}



16 Gate charge waveforms



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Revision History

Version	Date	Changes
1.1	08.04.2008	Page 1: VGS changed from ±16V to ±20V
1.1	08.04.2008	Page 3: Footnote 2) added